# CM1248-04S9

## Low Capacitance Transient Voltage Suppressors / ESD Protectors

## Features

- Low I/O Capacitance at 10 pF at 0 V
- In-System ESD Protection to ±15 kV Contact Discharge, per the IEC 61000-4-2 International Standard
- Compact SMT Package Saves Board Space and Facilitates Layout in Space–Critical Applications
- Each I/O Pin Can Withstand over 1000 ESD Strikes
- These Devices are Pb-Free and are RoHS Compliant



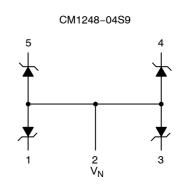
## **ON Semiconductor®**

http://onsemi.com



SOT-953 S9 SUFFIX CASE 527AE





## MARKING DIAGRAM



L8 = Specific Device Code M = Month Code

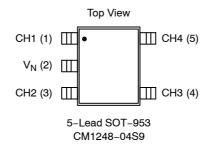
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
CM1248-04S9	SOT-953 (Pb-Free)	8000/Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## CM1248-04S9

## PACKAGE / PINOUT DIAGRAM



#### **Table 1. PIN DESCRIPTIONS**

Pins	Name	Description
(Refer to package / pinout diagram)	CHx	The cathode of the respective TVS diode, which should be connected to the node requiring transient voltage protection.
(Refer to package / pinout diagram)	V <sub>N</sub>	The anode of the TVS diodes.

## **SPECIFICATIONS**

#### Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units	
Storage Temperature Range	-65 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Table 3. STANDARD OPERATING CONDITIONS**

Parameter	Rating	Units	
Operating Temperature	-40 to +85	°C	

## Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
C <sub>IN</sub>	Channel Input Capacitance	T <sub>A</sub> = 25°C, 0 VDC, 1 MHz		10	13	pF
$\Delta C_{IN}$	Differential Channel I/O to GND Capacitance	T <sub>A</sub> = 25°C, 2.5 VDC, 1 MHz		0.19		pF
V <sub>RSO</sub>	Reverse Stand-off Voltage	I <sub>R</sub> = 10 μA, T <sub>A</sub> = 25°C	5.5			V
		I <sub>R</sub> = 1 mA, T <sub>A</sub> = 25°C	6.1			V
I <sub>LEAK</sub>	Leakage Current	$V_{IN}$ = 5.0 VDC, $T_A$ = 25°C			0.75	μA
V <sub>SIG</sub>	Small Signal Clamp Voltage Positive Clamp Negative Clamp	I = 10 mA, T <sub>A</sub> = 25°C I = −10 mA, T <sub>A</sub> = 25°C		6.8 -0.89		V
V <sub>ESD</sub>	ESD Withstand Voltage Contact Discharge per IEC 61000-4-2 Standard Human Body Model, MIL-STD-883, Method 3015	$T_A = 25^{\circ}C$ (Notes 3 and 4) $T_A = 25^{\circ}C$ (Notes 2 and 4)	±15 ±30			kV
R <sub>D</sub>	Diode Dynamic Resistance Forward Conduction Reverse Conduction	T <sub>A</sub> = 25°C (Note 2)		0.57 1.36		Ω

1. All parameters specified at  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$  unless otherwise noted. 2. Human Body Model per MIL-STD-883, Method 3015,  $C_{Discharge} = 100 \text{ pF}$ ,  $R_{Discharge} = 1.5 \text{ K}\Omega$ ,  $V_N$  grounded. 3. Standard IEC 61000-4-2 with  $C_{Discharge} = 150 \text{ pF}$ ,  $R_{Discharge} = 330 \Omega$ ,  $V_N$  grounded. 4. These measurements performed with no external capacitor on  $CH_X$ .

## CM1248-04S9

## **PERFORMANCE INFORMATION**

### **Diode Capacitance**

Typical diode capacitance with respect to positive TVS cathode voltage (reverse voltage across the diode) is given in Diode Capacitance vs. Reverse Voltage.

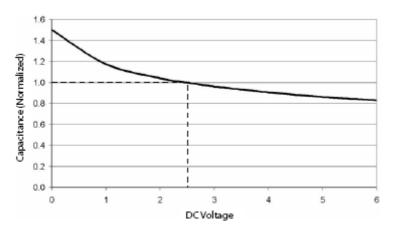


Figure 1. Diode Capacitance vs. Reverse Voltage

### **Typical High Current Diode Characteristics**

Measurements are made in pulsed mode with a nominal pulse width of 0.7 ms.

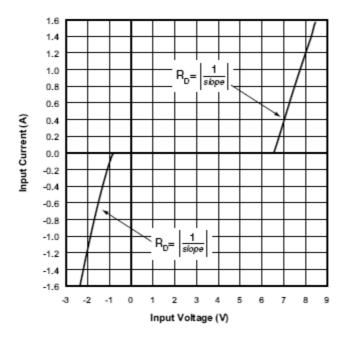
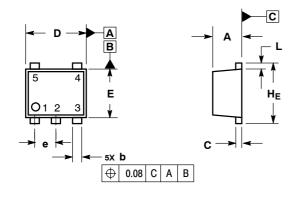


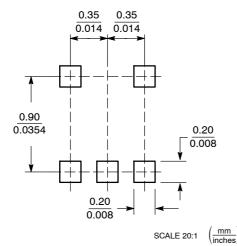
Figure 2. Typical Input VI Characteristics (Pulse-mode Measurements, Pulse Width = 0.7 ms nominal)

#### PACKAGE DIMENSIONS

SOT-953 CASE 527AE-01 ISSUE D



SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

MILLIMETERS			INCHES			
MIN	NOM	MAX	MIN	NOM	MAX	
0.34	0.37	0.40				
0.10	0.15	0.20	0.004	0.006	0.008	
0.07	0.12	0.17	0.003	0.005	0.007	
0.95	1.00	1.05	0.037	0.039	0.041	
0.75	0.80	0.85	0.03	0.032	0.034	
0.35 BSC			0.014 BSC			
0.05	0.10	0.15	0.002	0.004	0.006	
0.95	1.00	1.05	0.037	0.039	0.041	
	MIN 0.34 0.10 0.07 0.95 0.75 0.05	MIN NOM   0.34 0.37   0.10 0.15   0.07 0.12   0.95 1.00   0.75 0.80   0.35 BS 0.05	MIN NOM MAX   0.34 0.37 0.40   0.10 0.15 0.20   0.07 0.12 0.17   0.95 1.00 1.05   0.75 0.80 0.85   0.35 BSC 0.05 0.15	MIN NOM MAX MIN   0.34 0.37 0.40 0.10 0.15 0.20 0.004   0.10 0.15 0.20 0.004 0.07 0.12 0.17 0.003   0.95 1.00 1.05 0.037 0.35 0.03 0.35 BSC 0   0.05 0.10 0.15 0.002 0.020 0.022 0.022	MIN NOM MAX MIN NOM   0.34 0.37 0.40 -	